

**ABSTRACT OF THE DISCLOSURE**

5 The present invention is directed to a method for fabricating a metal line of a semiconductor device. The method comprises the steps of forming an insulation layer, a metal layer and an organic anti-reflection coating in order on a semiconductor substrate on which devices or lower lines are formed, forming a photoresist pattern having an opening of certain width on the organic anti-reflection coating, forming a buffer layer of certain thickness on the photoresist pattern, and selectively removing the metal layer at a lower side of the opening by performing a dry etching process.

10